C6D10065A

Silicon Carbide Schottky Diode

Z-Rec® Rectifier

V_{RRM}	=	650 V
I_F (T_C=155˚C)	=	10 A
Q_c	=	34 nC

Features

- New 6th Generation Technology
- Low Forward Voltage Drop (V_F)
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Low Leakage Current (I_r)
- Temperature-Independent Switching Behavior
- Positive Temperature Coefficient on V_F

Package

TO-220-2

Halogen-Free

RoHS

Benefits

- Higher System Level Efficiency
- Increase System Power Density
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Server/Telecom Power Supplies
- Industrial Power Supplies
- Solar
- UPS

Part Number	Package	Marking
C6D10065A	TO-220-2	C6D10065

Maximum Ratings (T_C = 25 ˚C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	650	V		
V_{DC}	DC Blocking Voltage	650	V		
I_F	Continuous Forward Current	37 19 10	A	T_C=25˚C T_C=125˚C T_C=155˚C	Fig. 3
I_{FRM}	Repetitive Peak Forward Surge Current	45 27	A	T_C=25˚C, t_P = 10 ms, Half Sine Wave T_C=110˚C, t_P=10 ms, Half Sine Wave	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	86 75	A	T_C=25˚C, t_p = 10 ms, Half Sine Wave T_C=110˚C, t_p = 10 ms, Half Sine Wave	Fig. 8
$I_{F,Max}$	Non-Repetitive Peak Forward Surge Current	1250 1100	A	T_C=25˚C, t_P = 10 µs, Pulse T_C=110˚C, t_P = 10 µs, Pulse	Fig. 8
P_{tot}	Power Dissipation	109 47	W	T_C=25˚C T_C=110˚C	Fig. 4
T_J , T_{stg}	Operating Junction and Storage Temperature	-55 to +175	˚C		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.27 1.37	1.50 1.60	V	I_F = 10 A T_J=25°C I_F = 10 A T_J=175°C	Fig. 1
I_R	Reverse Current	2 15	50 200	μA	V_R = 650 V T_J=25°C V_R = 650 V T_J=175°C	Fig. 2
Q_C	Total Capacitive Charge	34		nC	V_R = 400 V, I_F = 10A T_J = 25°C	Fig. 5
C	Total Capacitance	611 67 53		pF	V_R = 0 V, T_J = 25°C, f = 1 MHz V_R = 200 V, T_J = 25°C, f = 1 MHz V_R = 400 V, T_J = 25°C, f = 1 MHz	Fig. 6
E_C	Capacitance Stored Energy	5.2		μJ	V_R = 400 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.38	°C/W	Fig. 9

Typical Performance

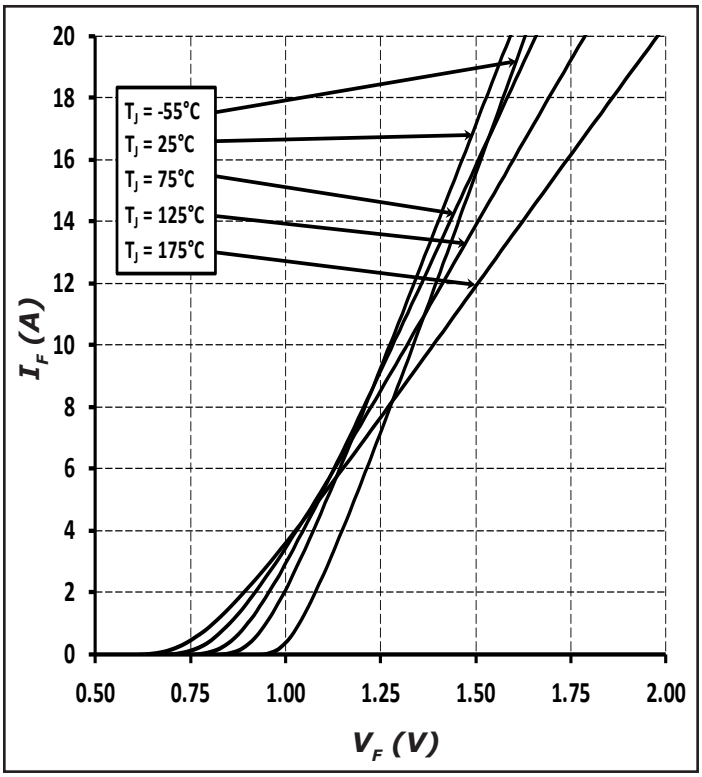


Figure 1. Forward Characteristics

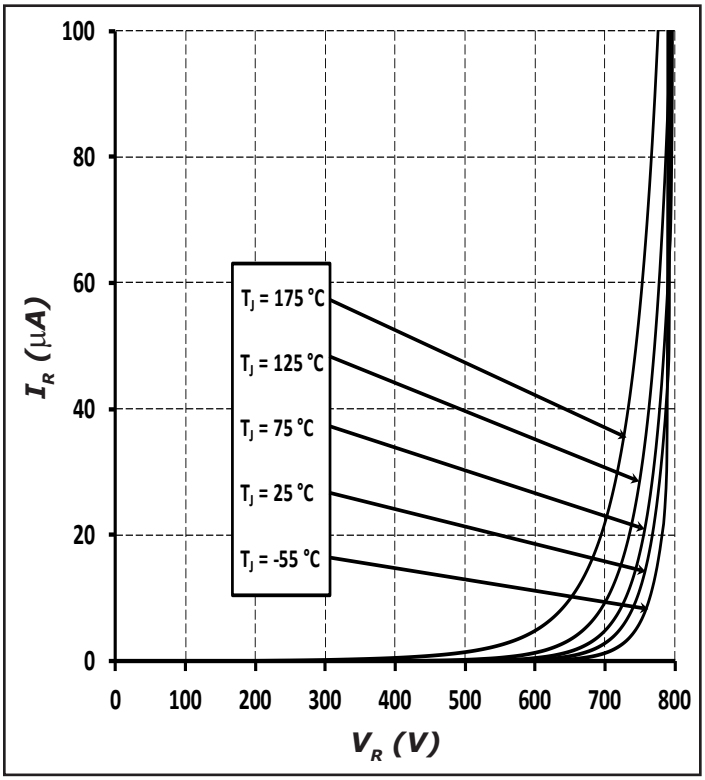


Figure 2. Reverse Characteristics

Typical Performance

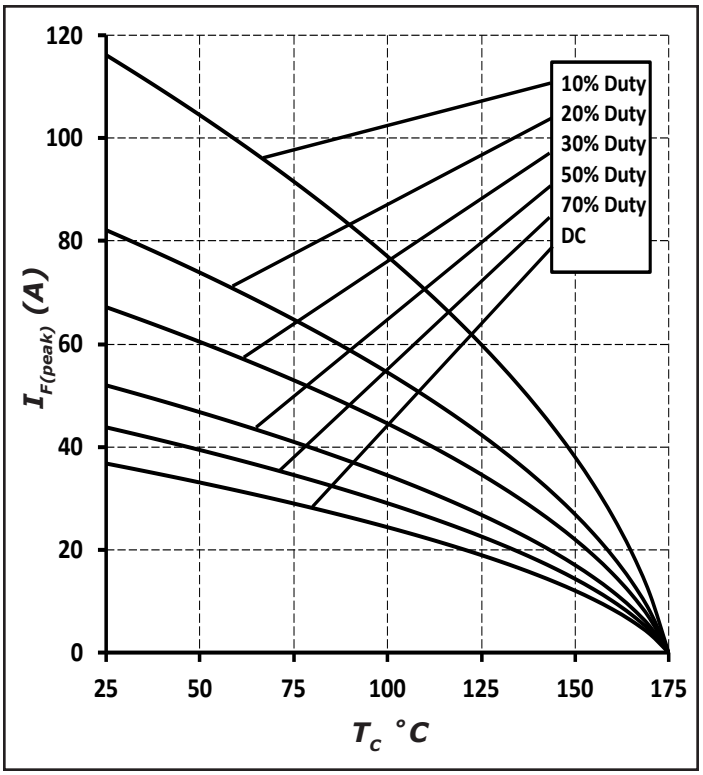


Figure 3. Current Derating

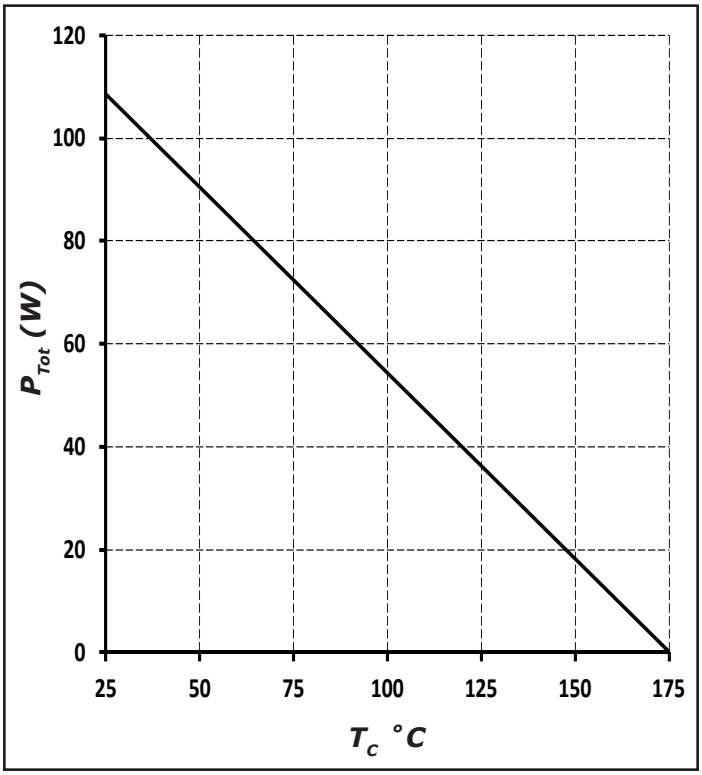


Figure 4. Power Derating

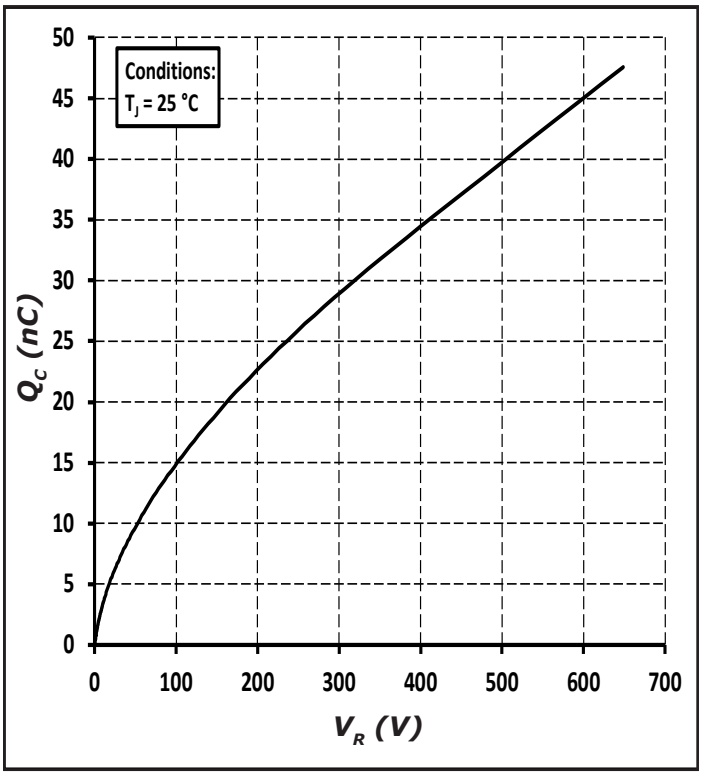


Figure 5. Total Capacitance Charge vs. Reverse Voltage

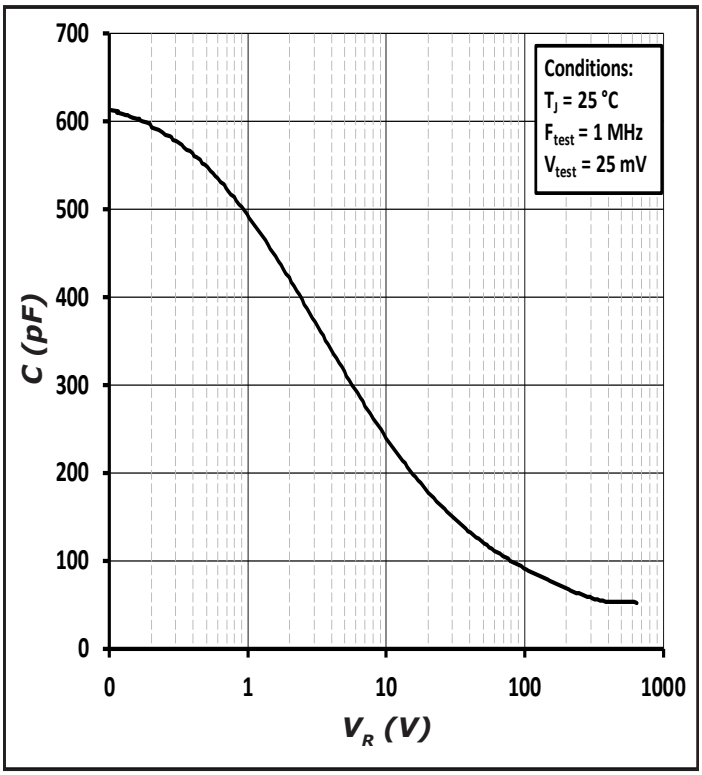


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

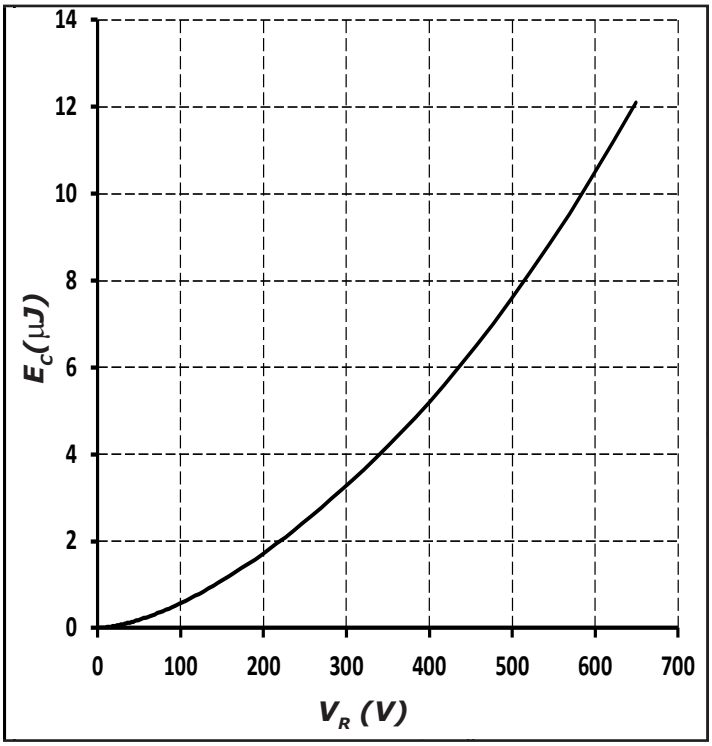


Figure 7. Capacitance Stored Energy

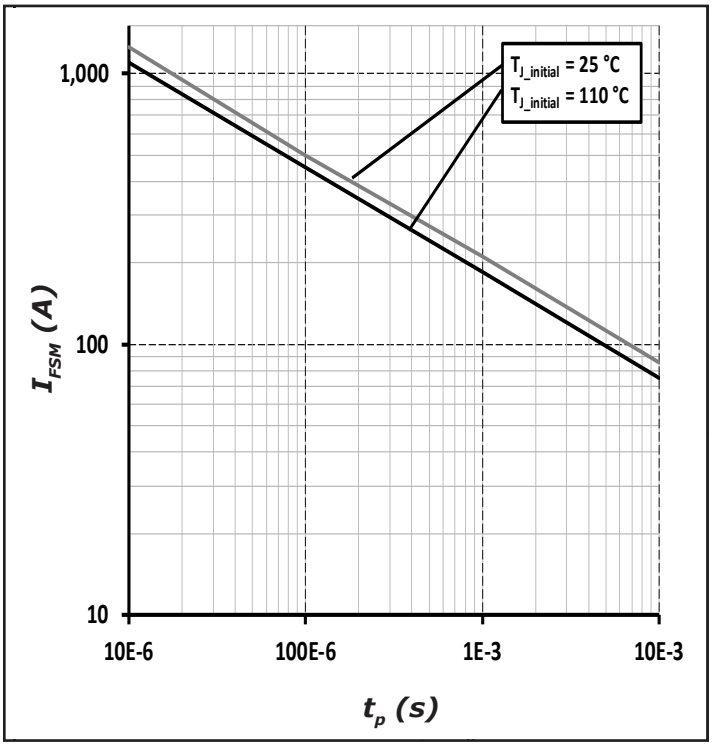


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

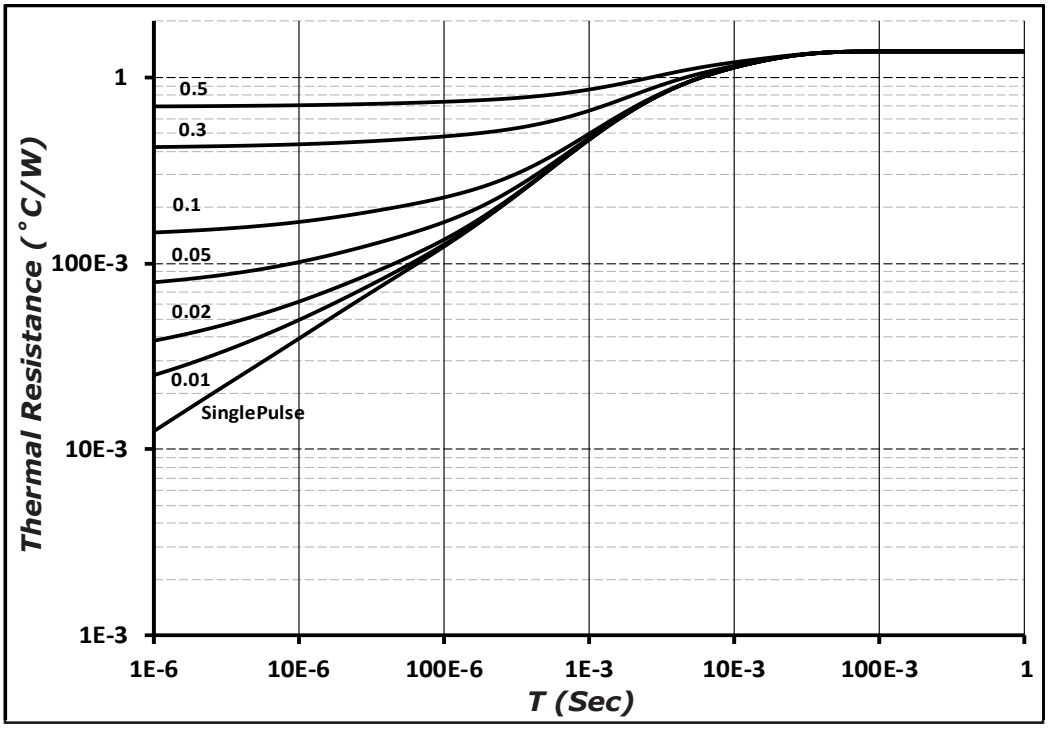
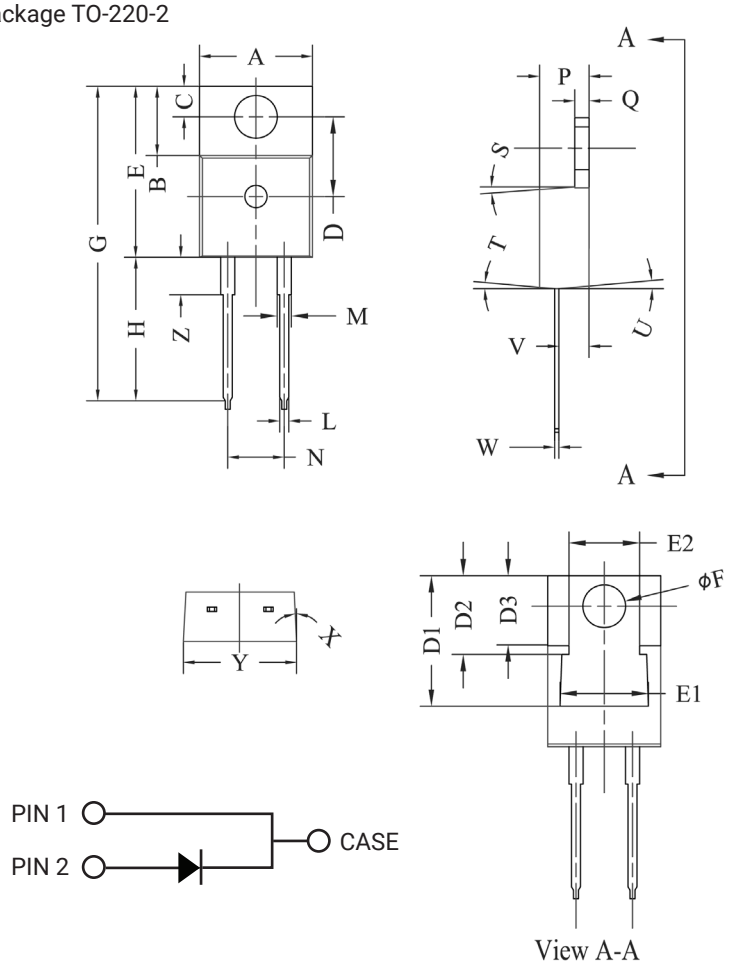


Figure 9. Transient Thermal Impedance

Package Dimensions

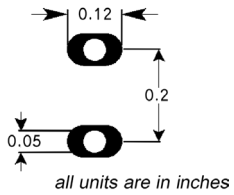
Package TO-220-2



POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.381	.410	9.677	10.414
B	.235	.255	5.969	6.477
C	.100	.120	2.540	3.048
D	.223	.337	5.664	8.560
D1	.457-.490		11.60-12.45 typ	
D2	.277-.303 typ		7.04-7.70 typ	
D3	.244-.252 typ		6.22-6.4 typ	
E	.590	.615	14.986	15.621
E1	.302	.326	7.68	8.28
E2	.227	251	5.77	6.37
F	.143	.153	3.632	3.886
G	1.105	1.147	28.067	29.134
H	.500	.550	12.700	13.970
L	.025	.036	.635	.914
M	.045	.055	1.143	1.550
N	.195	.205	4.953	5.207
P	.165	.185	4.191	4.699
Q	.048	.054	1.219	1.372
S	3°	6°	3°	6°
T	3°	6°	3°	6°
U	3°	6°	3°	6°
V	.094	.110	2.388	2.794
W	.014	.025	.356	.635
X	3°	5.5°	3°	5.5°
Y	.385	.410	9.779	10.414
z	.130	.150	3.302	3.810

NOTE:
1. Dimension L, M, W apply for Solder Dip Finish

Recommended Solder Pad Layout



TO-220-2

Part Number	Package	Marking
C6D10065A	TO-220-2	C6D10065

Note: Recommended soldering profiles can be found in the applications note here:
http://www.wolfspeed.com/power_app_notes/soldering

Notes

- **RoHS Compliance**
  The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfpseed representative or from the Product Ecology section of our website at http://www.wolfspeed.com/Power/Tools-and-Support/Product-Ecology.

- **REACh Compliance**
  REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future,please contact a Cree representative to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control systems.

Related Links

- Cree SiC Schottky diode portfolio: http://www.wolfspeed.com/Power/Products#SiCSchottkyDiodes
- Schottky diode Spice models: http://www.wolfspeed.com/power/tools-and-support/DIODE-model-request2
- SiC MOSFET and diode reference designs: http://go.pardot.com/l/101562/2015-07-31/349i

Cree, Inc.
4600 Silicon Drive
Durham, NC 27703
USA Tel: +1.919.313.5300
Fax: +1.919.313.5451
www.cree.com/power